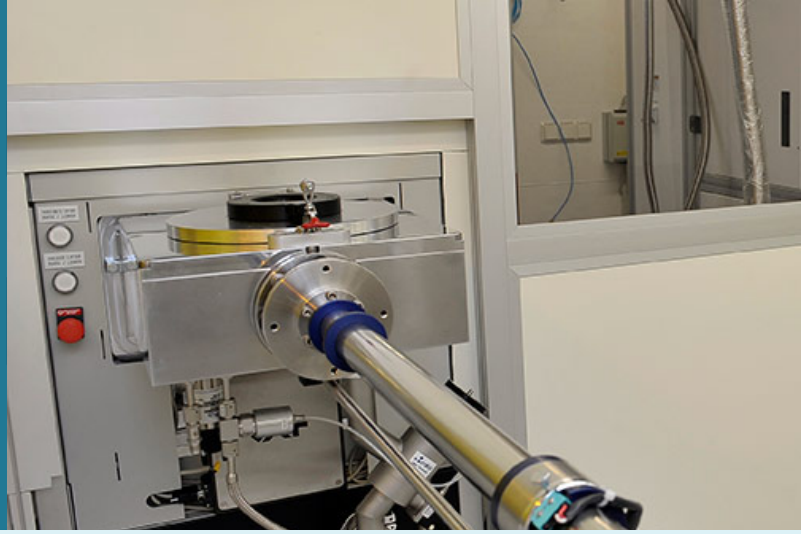


PROJECT FACTSHEET

www.list.lu/en/research/project/deptos/?no_cache=1&cHash=4bf9fb7f863f2c2306c6db0e23363eca

DEPTOS

Mastering the faults in type P transparent semiconductor oxides



INSPIRATION

Transparent and conducting thin layers are currently used extensively in several domains: low-emissivity windows, electrodes for solar cells, electrochromic mirrors, electromagnetic shields, etc. All of these devices are based on high conductivity ($S > 1000 \text{ S/cm}$) type n transparent semiconductor oxides. In 1997, the discovery of the first type p transparent semiconductors provided for a new perspective for the realization of active transparent items, constituted by a junction of p-n. Up to now, the best semiconductor oxide has been CuCrO_2 doped with Mg with a conductivity of 220 S/cm .

INNOVATION

The DEPTOS project focuses on improving the electrical conductivity and optical transmission for delafossite materials such as CuMO_2 ($M = \text{Cr}, \text{B}$). Three avenues for improvement are being studied:

- formation of Oxygen interstitials;
- formation of Copper gaps;
- combination of the two.

IMPACT

To improve the current performances of transparent oxide semiconductors, DEPTOS will propose a new approach involving ion implantation as a means of controlling the Fermi level in the envisaged semiconductors.

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